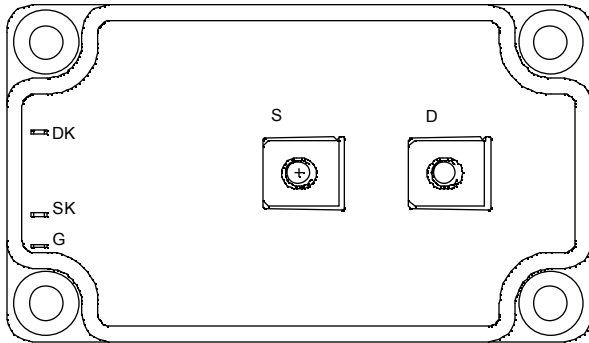
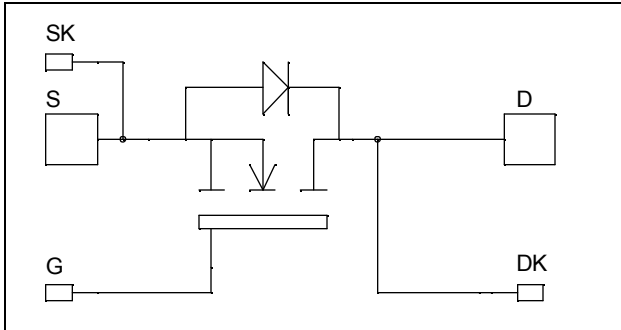


## Single Switch MOSFET Power Module

$V_{DSS} = 100V$   
 $R_{DSon} = 1.5m\Omega \text{ typ @ } T_j = 25^\circ C$   
 $I_D = 860A^* \text{ @ } T_c = 25^\circ C$



### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS V<sup>®</sup> FREDFETs
  - Low  $R_{DSon}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Fast intrinsic diode
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration
- AlN substrate for improved thermal performance

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{DSS}$	Drain - Source Breakdown Voltage	100	V
$I_D$	Continuous Drain Current	$T_c = 25^\circ C$	860 *
		$T_c = 80^\circ C$	640 *
$I_{DM}$	Pulsed Drain current	2200	
$V_{GS}$	Gate - Source Voltage	$\pm 30$	V
$R_{DSon}$	Drain - Source ON Resistance	1.6	$m\Omega$
$P_D$	Maximum Power Dissipation	$T_c = 25^\circ C$	2500
$I_{AR}$	Avalanche current (repetitive and non repetitive)	100	A
$E_{AR}$	Repetitive Avalanche Energy	50	mJ
$E_{AS}$	Single Pulse Avalanche Energy	3000	

\* Specification of MOSFET device but output current must be limited to 500A to not exceed a delta of temperature greater than 100°C for the connectors.

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 100V$			500	$\mu\text{A}$
		$V_{GS} = 0V, V_{DS} = 80V$			2000	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 275A$		1.5	1.6	$\text{m}\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 12\text{mA}$	2		4	V
$I_{GSS}$	Gate – Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			$\pm 450$	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$		60		nF
$C_{oss}$	Output Capacitance	$V_{DS} = 25V$		23		
$C_{rss}$	Reverse Transfer Capacitance	$f = 1\text{MHz}$		8.8		
$Q_g$	Total gate Charge	$V_{GS} = 10V$		2100		nC
$Q_{gs}$	Gate – Source Charge	$V_{Bus} = 50V$		360		
$Q_{gd}$	Gate – Drain Charge	$I_D = 550A$		1080		
$T_{d(on)}$	Turn-on Delay Time	<b>Inductive switching</b> $V_{GS} = 15V$ $V_{Bus} = 66V$ $I_D = 550A$ $R_G = 1\Omega$		185		ns
$T_r$	Rise Time			270		
$T_{d(off)}$	Turn-off Delay Time			600		
$T_f$	Fall Time			175		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 25°C</b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 550A, R_G = 1\Omega$		3.3		mJ
$E_{off}$	Turn-off Switching Energy			3.6		
$E_{on}$	Turn-on Switching Energy	<b>Inductive switching @ 125°C</b> $V_{GS} = 15V, V_{Bus} = 66V$ $I_D = 550A, R_G = 1\Omega$		3.65		mJ
$E_{off}$	Turn-off Switching Energy			3.85		

**Source - Drain diode ratings and characteristics**

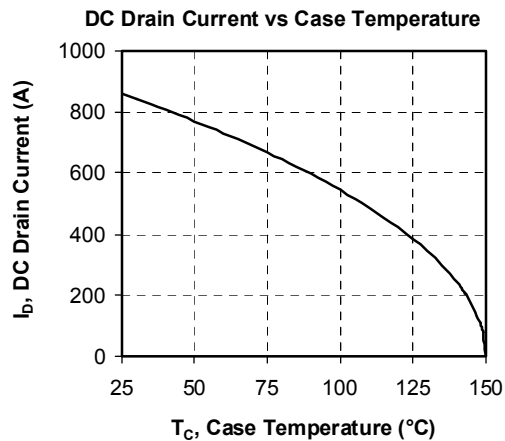
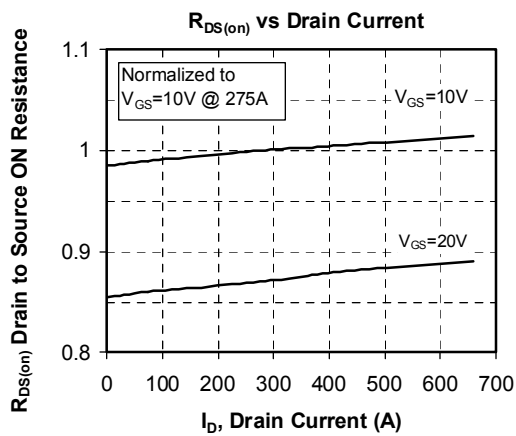
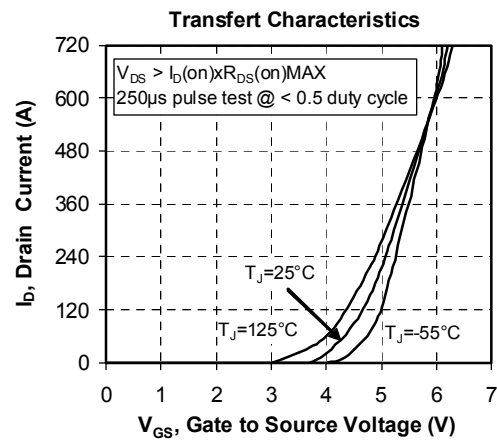
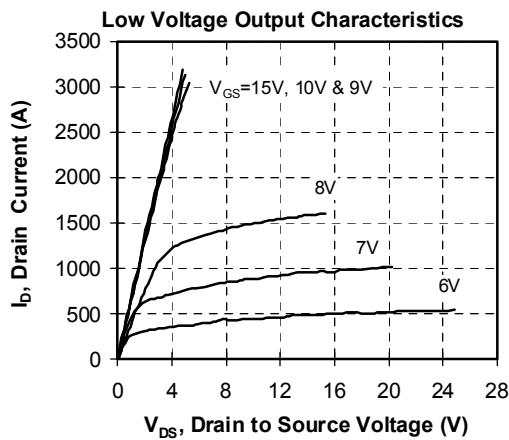
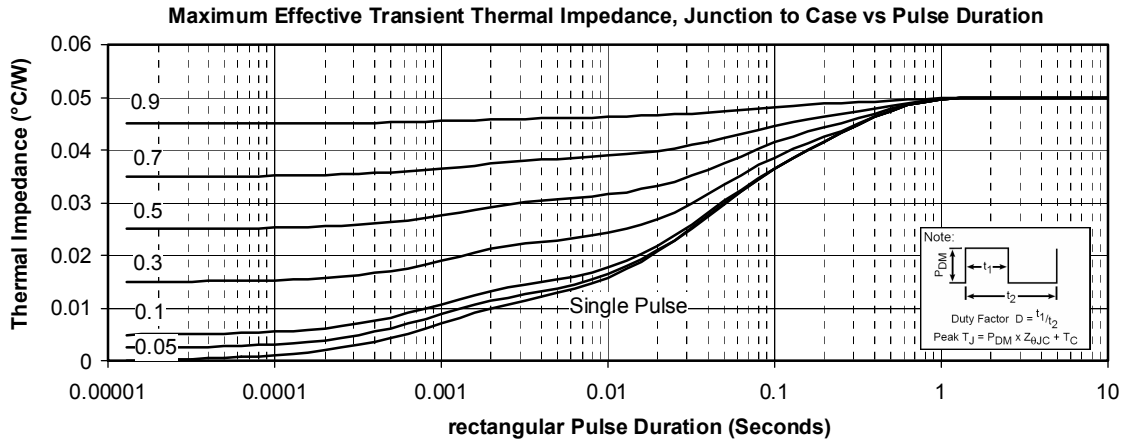
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$I_S$	Continuous Source current (Body diode)	$T_c = 25^\circ\text{C}$			860*	A	
		$T_c = 80^\circ\text{C}$			640*		
$V_{SD}$	Diode Forward Voltage	$V_{GS} = 0V, I_S = -550A$			1.3	V	
$dv/dt$	Peak Diode Recovery ①				5	V/ns	
$t_{rr}$	Reverse Recovery Time	$I_S = -550A$ $V_R = 66V$ $di/dt = 600A/\mu\text{s}$	$T_j = 25^\circ\text{C}$			190	ns
			$T_j = 125^\circ\text{C}$			370	
$Q_{rr}$	Reverse Recovery Charge	$I_S = -550A$ $V_R = 66V$ $di/dt = 600A/\mu\text{s}$	$T_j = 25^\circ\text{C}$		2.4	$\mu\text{C}$	
			$T_j = 125^\circ\text{C}$		10.2		

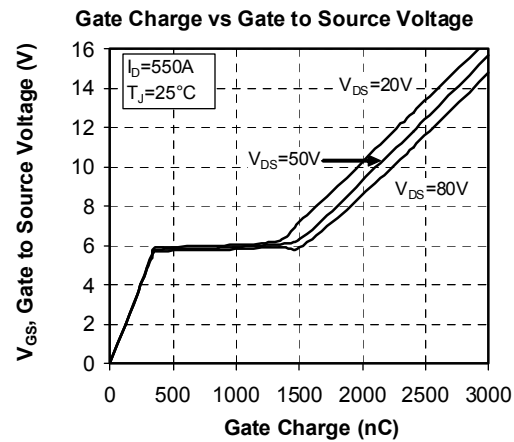
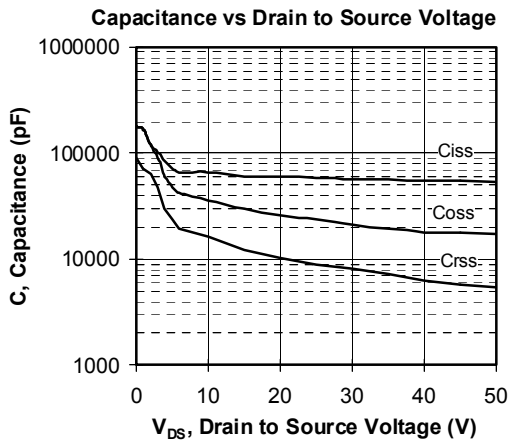
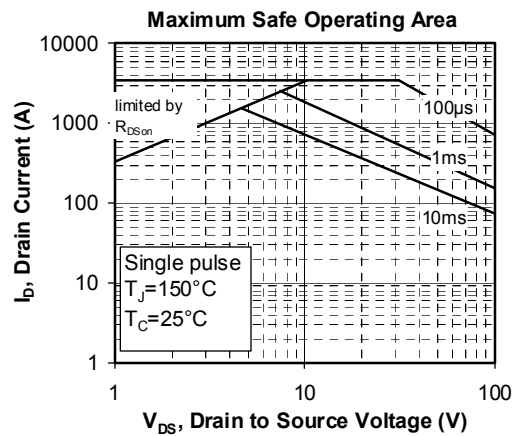
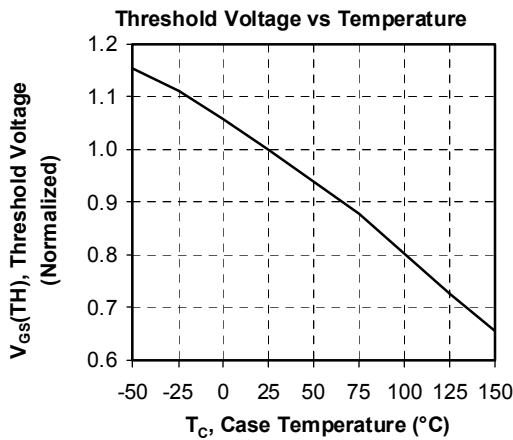
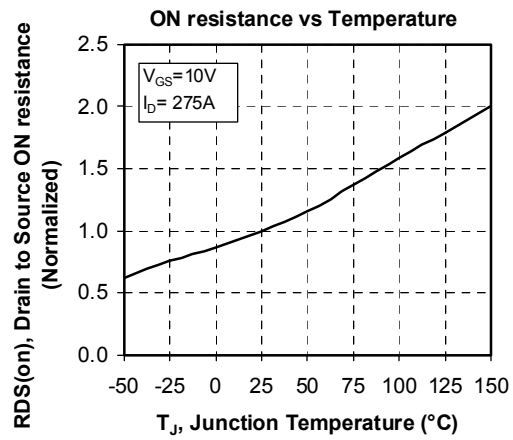
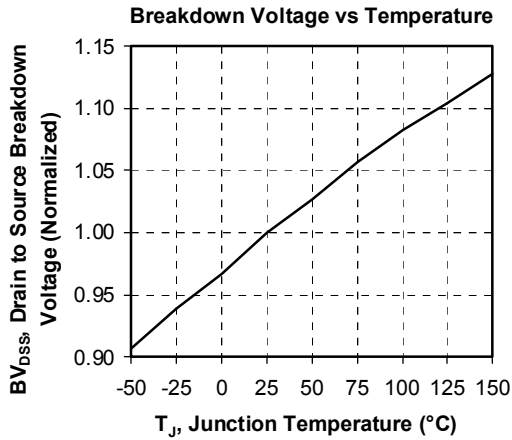
 ①  $dv/dt$  numbers reflect the limitations of the circuit rather than the device itself.

$$I_S \leq -860A \quad di/dt \leq 600A/\mu\text{s} \quad V_R \leq V_{DSS} \quad T_j \leq 150^\circ\text{C}$$

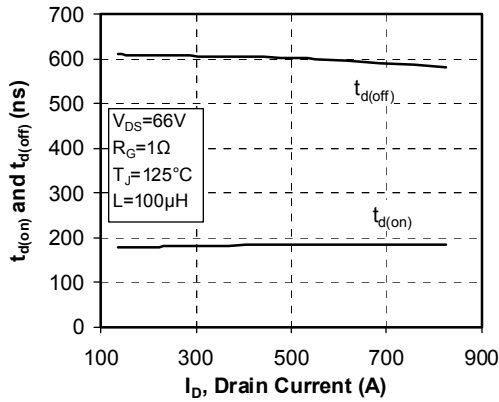


## Typical Performance Curve

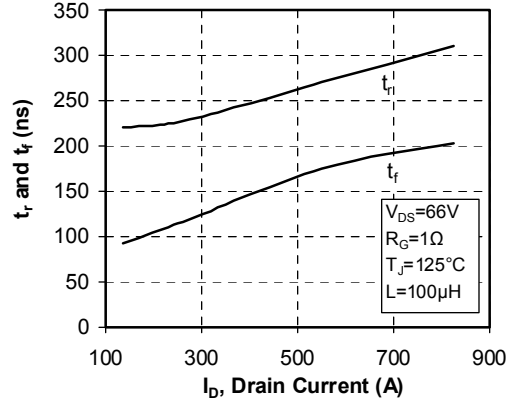




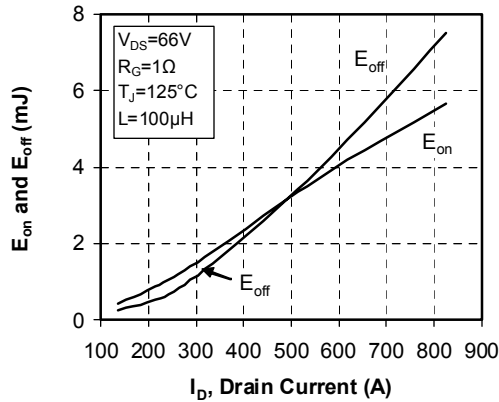
**Delay Times vs Current**



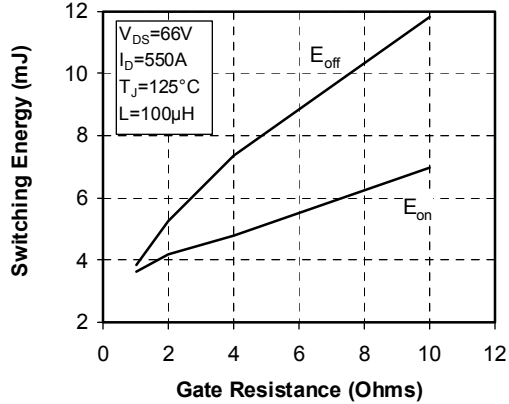
**Rise and Fall times vs Current**



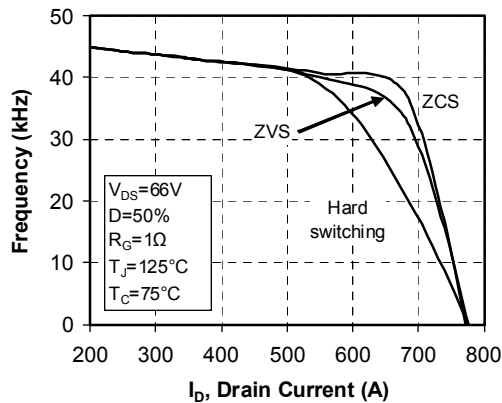
**Switching Energy vs Current**



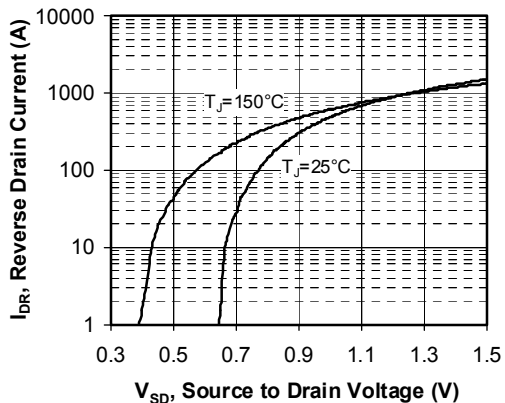
**Switching Energy vs Gate Resistance**



**Operating Frequency vs Drain Current**



**Source to Drain Diode Forward Voltage**



Microsemi reserves the right to change, without notice, the specifications and information contained herein

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